

**Room H #108** 10:45-12:45**[Fr-H2] Interface Engineering/Epitaxy****Session Chairs:**

Jang-Sik Lee (POSTECH, Korea)

Fr-H2-1 10:45-11:00**Two-Dimensional Electron Gas Characteristics of AlGaN/GaN HEMTs with AlN Insert Layer on 4H-SiC Grown by MOCVD**

Jaeyeon Han, Kyeongjae Lee, Uiho Choi, Yongjun Nam, Taehoon Jang, and Okhyun Nam

*Korea Polytechnic Univ., Korea***Fr-H2-2** 11:00-11:15**Selective Silicon Epitaxy via Plasma-Enhanced Chemical Vapor Deposition at Atmospheric Pressure**Hwayeon Ryu¹, Changhun Song¹, Hyunsu Shin¹, Seran Park¹, Won Ki Cho², Seung Jae Baik², Hoonjung Oh¹, and Dae-Hong Ko¹¹*Yonsei Univ., Korea*, ²*Hankyong Nat'l Univ., Korea***Fr-H2-3** 11:15-11:30**BeCaZnO Quaternary Alloys: Epitaxial Film Growth and Ultraviolet Photodetector Fabrication**

Teng Zhang, Mingkai Li, Yang Cheng, Wuzhong Zhang, Yinmei Lu, and Yunbin He

*Hubei Univ., China***Fr-H2-4** 11:30-11:45**The Properties of $Zr_xSn_{1-x}O_2$ Semiconductor Alloy Epitaxial Thin Film and its Application in Ultraviolet Photodetector**

Yang Cheng, Mingkai Li, Debing Long, Jian Chen, Teng Zhang, Dongxue Meng, Yinmei Lu, and Yunbin He

*Hubei Univ., China***Fr-H2-5** 11:45-12:00**UV Detectors based on High-Quality $Be_xZn_{1-x}O_{1-y}S_y$ Alloy Films**

Wuzhong Zhang, Mingkai Li, Yinmei Lu, Ronghuizi Yang, Teng Zhang, and Yunbin He

*Hubei Univ., China***Fr-H2-6** 12:00-12:15**Study of Atomic Arrangements and Charge Distribution on Si(001) Surfaces with the Adsorption of One Ge Atom by DFTB Calculations**Lin Zhang¹ and Lijun Wu²¹*Northeastern Univ., China*, ²*Shenyang Ligong Univ., China*